IGBT Modules and Applications (ZJU-FJU BDU SEMINAR)

时间：2018 年 6 月 29 日（周五）下午 2 点至 5 点
地点：浙江大学玉泉校区电机工程楼 408 室

内容：

14:00-14:10 Greeting, Introduction of Fuji Semiconductor Business,
Speaker: Naoto Fujishima, Fuji Electric Co., Ltd
14:10-14:40 High I2t capability power modules for x EV power train with leadframe and RC-IGBT combination,
Speaker: Akihiro Osawa, Fuji Electric Co., Ltd.
14:40-15:05 High power next Core(HPnC) package with 3.3kV SiC Hybrid chip combination,
Speaker: Yusuke Sekino, Fuji Electric Co., Ltd.
15:05-15:30 1,700V IGBT module with newly developed 7th Generation technology,
Speaker: Song Chen, Fuji Electric (China) Co., Ltd
15:30-15:40 Short Break
15:40-16:05 Influence of negative voltage between gate and emitter to the turn-off behavior of IGBT device,
Speaker: Fumio Yukawa, Fuji Electric Co., Ltd
16:05-16:30 Expansion of power rating with 7th-Generation “X Series” RC-IGBT Modules for Industrial Applications,
Speaker: Akio Yamano, Fuji Electric Co., Ltd
16:30-16:40 Q&A and Closing

欢迎各位老师、本科高年级及研究生同学积极参加！

电气工程学院应用电子学系
2018. 6